Power MOSFET -12V, 84mΩ, -3A, Single P-Channel

This Low-profile High-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

Features

- Low On-Resistance
- High speed switching
- 1.8V drive
- Low capacitance
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

Typical Applications

- Battery Switch
- Load Switch
- DC/DC Converter
- Lens Motor Driver

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-12	V
Gate to Source Voltage	VGSS	±10	٧
Drain Current (DC)	ID	-3	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	-12	Α
Power Dissipation When mounted on ceramic substrate (900mm² × 0.8mm)	PD	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

THERMAL REGIOTANCE NATINGO						
Parameter	Symbol	Value	Unit			
Junction to Ambient When mounted on ceramic substrate (900mm ² × 0.8mm)	$R_{ heta JA}$	125	°C/W			

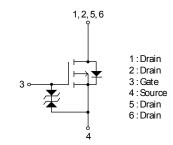


ON Semiconductor®

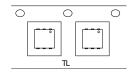
www.onsemi.com

VDSS	RDS(on) Max	ID Max
	84mΩ@ -4.5V	
-12V	126mΩ@ –2.5V	-3A
	230mΩ@ -1.8V	

ELECTRICAL CONNECTION P-Channel



PACKING TYPE: TL MARKING





ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

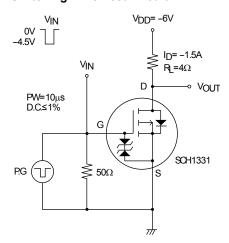
^{2 :} This product is designed to "ESD immunity < 200V*", so please take care when handling. *Machine Model

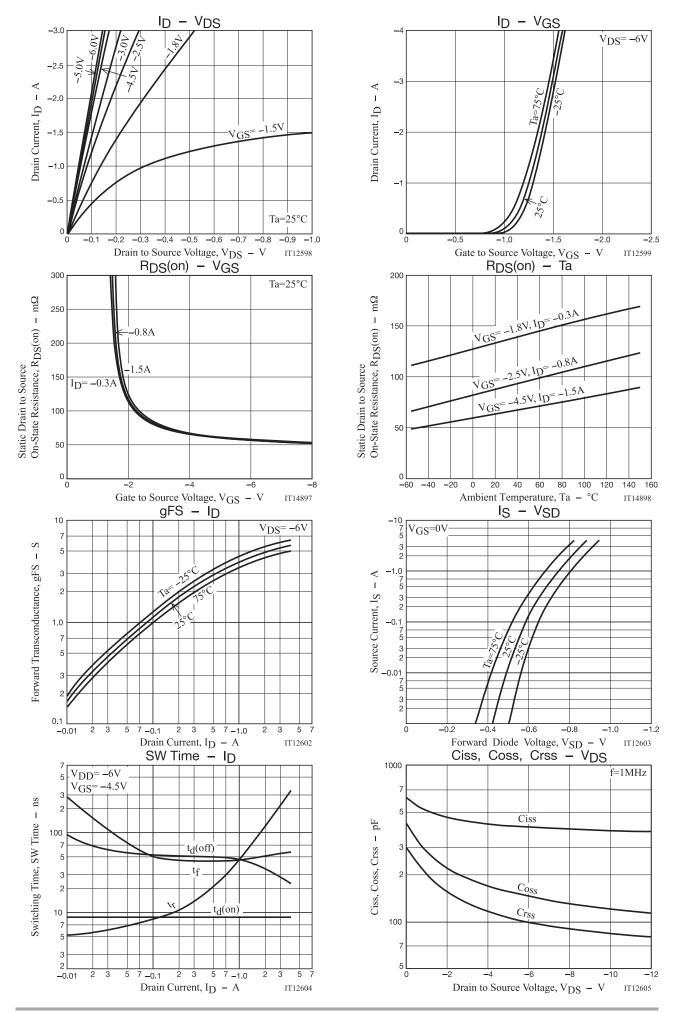
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

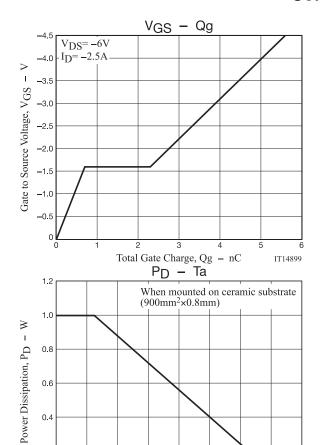
Parameter	Symbol	Conditions	Value			Unit
Farameter	Symbol	Conditions	min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0V	-12			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _G S(th)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.3	V
Forward Transconductance	gFS	V _{DS} =-6V, I _D =-1.5A	2.7	4.5		S
	R _{DS} (on)1	I _D =-1.5A, V _G S=-4.5V		64	84	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =-0.8A, V _G S=-2.5V		90	126	mΩ
Resistance	R _{DS} (on)3	I _D =-0.3A, V _G S=-1.8V		135	230	mΩ
Input Capacitance	Ciss			405		pF
Output Capacitance	Coss	V _{DS} =–6V, f=1MHz		145		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	t _d (on)			8.8		ns
Rise Time	tr	Con annuitied Took Circuit		80		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		41		ns
Fall Time	tf			50		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-2.5A		0.7		nC
Gate to Drain "Miller" Charge	Qgd			1.6		nC
Forward Diode Voltage	V _{SD}	I _S =-2.5A, V _{GS} =0V		-0.82	-1.2	V

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

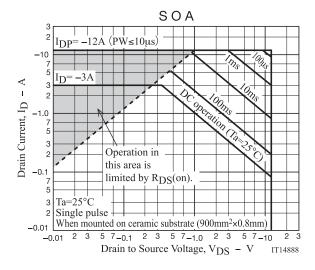
Switching Time Test Circuit

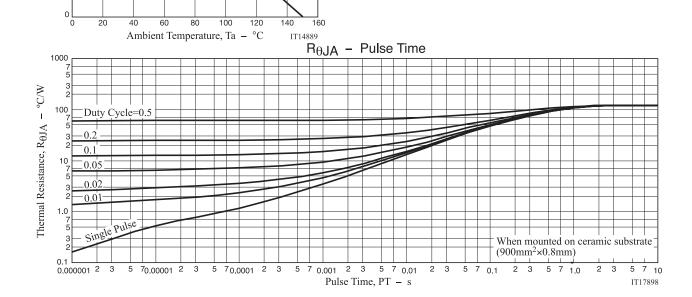






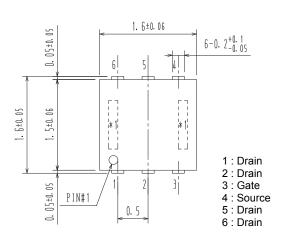
0.2

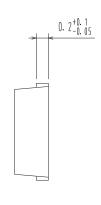


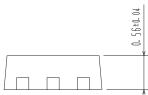


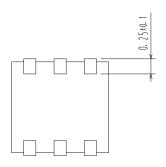
PACKAGE DIMENSIONS

unit : mm SOT-563 / SCH6 CASE 463AB ISSUE O

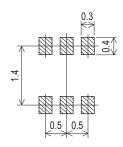








Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)		
SCH1331-TL-H	YG	SOT-563 / SCH6	5 000 / Tono 9 Dool		
SCH1331-TL-W	16	(Pb-Free / Halogen Free)	5,000 / Tape & Reel		

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the SCH1331 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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